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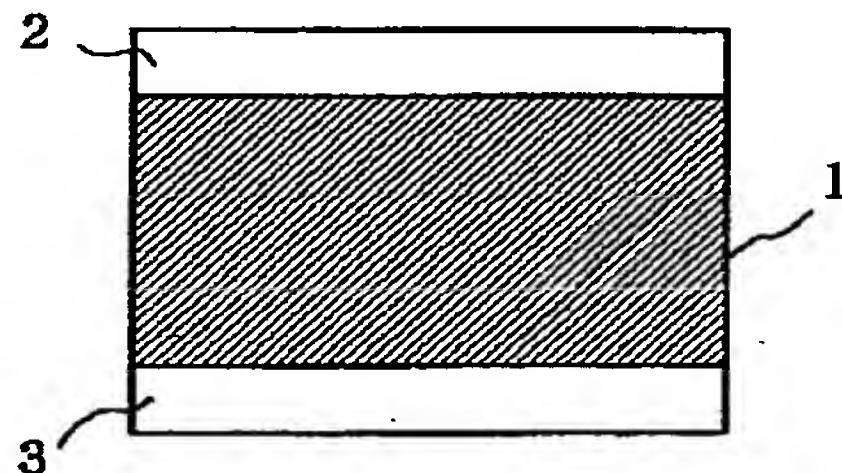
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(54)【発明の名称】 温度センサー

(57)【要約】

【目的】 簡単に、精度よく温度を測定する。

【構成】 ある温度で絶縁体-金属相転移を起こすヴァ  
ナジウム酸化物 ( $V_2 O_3$ ) 膜1の上面および下面に銅  
2, 3を蒸着することでサンドイッチ構造にし、全体を  
被測温物に張り付けて銅2, 3間の抵抗を測定できるよ  
うにする。

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## 【特許請求の範囲】

【請求項1】ある温度で絶縁体-金属相転移を起こす物質と、前記物質を挟み込む金属とからなることを特徴とする温度センサー。

## 【発明の詳細な説明】

## 【0001】

【産業上の利用分野】本発明は、温度センサーに関するものである。

## 【0002】

【従来の技術】従来、温度を測定する場合に温度センサーとしては、液体の熱膨張を利用した液体温度計、気体などの圧力の温度変化を利用した圧力温度計、熱放射を利用した放射温度計、熱起電力を利用した熱電対温度計などが、「理科学辞典」、第4版、1991年刊行、191頁に報告されている。

## 【0003】

【発明が解決しようとする課題】しかしながら、上記の従来の温度センサーは、温度変化に対するセンサー出力の変化がわずかなために、それを精度よく観測することができないという問題点があった。

【0004】さらに、ある温度を観測して、一定以上、あるいは一定以下でスイッチを入れたり、切ったりする場合には、温度センサーからのシグナルを電気信号に変えなければならず、複雑になるという問題点があった。

【0005】本発明の目的は、このような従来の問題点を解決し、簡単に、精度よく温度を測定することができる温度センサーを提供することにある。

## 【0006】

【課題を解決するための手段】本発明は、ある温度で絶縁体-金属相転移を起こす物質と、前記物質を挟み込む金属とからなることを特徴としている。

## 【0007】

【実施例】次に、本発明の実施例について図面を参照して説明する。

【0008】図1は、本発明の温度センサーの一実施例を示す横断面図である。図1に示す温度センサーは、あ

る温度で絶縁体-金属相転移（モット一転移）を起こす物質であるヴァナジウム酸化物（ $V_2O_3$ ）を膜状にしたヴァナジウム酸化物（ $V_2O_3$ ）膜1の上面および下面に、金属である銅（Cu）2, 3を蒸着することでサンドイッチ構造にしたものであり、全体を被測温物に張り付け、銅2, 3間の抵抗を測定できるようにしたものである。

【0009】ヴァナジウム酸化物（ $V_2O_3$ ）膜1が絶縁体の場合には、膜間には電流は流れないが、ある温度 $T_c$ で金属に相転移が起こった場合には、 $10^7$ 程度の抵抗変化があり、非常に簡単に相転移が起こったことを観測することができる。この相転移を起こす温度 $T_c$ は、ヴァナジウム酸化物（ $V_2O_3$ ）膜1に固有のものであり、正確に一つの値に定められる。ゆえに、抵抗変化を測定することで、正確に温度を測定することができる。

【0010】図2は、本実施例の膜間の抵抗値の温度変化を示す図であり、 $150^{\circ}C$ で金属から絶縁体に相転移しているのがわかる。

## 【0011】

【発明の効果】以上説明したように本発明は、相転移に伴った抵抗変化が $10^7$ 程度となるために、温度によって絶縁体-金属相転移を起こす物質を金属で挟んだものの抵抗を測定することによって、非常に簡単に、しかも正確に温度を測定することができるとともに、この抵抗変化をそのまま電流変化に変換することができ、温度変化を利用したスイッチに利用することができるという効果を有する。

## 【図面の簡単な説明】

【図1】本発明の温度センサーの一実施例を示す横断面図である。

【図2】本実施例の膜間の抵抗値の温度変化を示す図である。

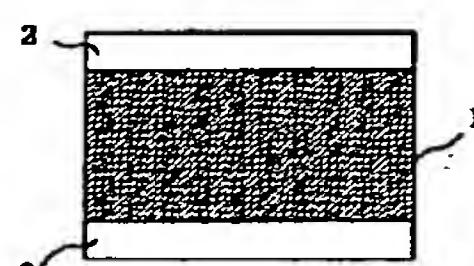
## 【符号の説明】

1 ヴァナジウム酸化物（ $V_2O_3$ ）膜

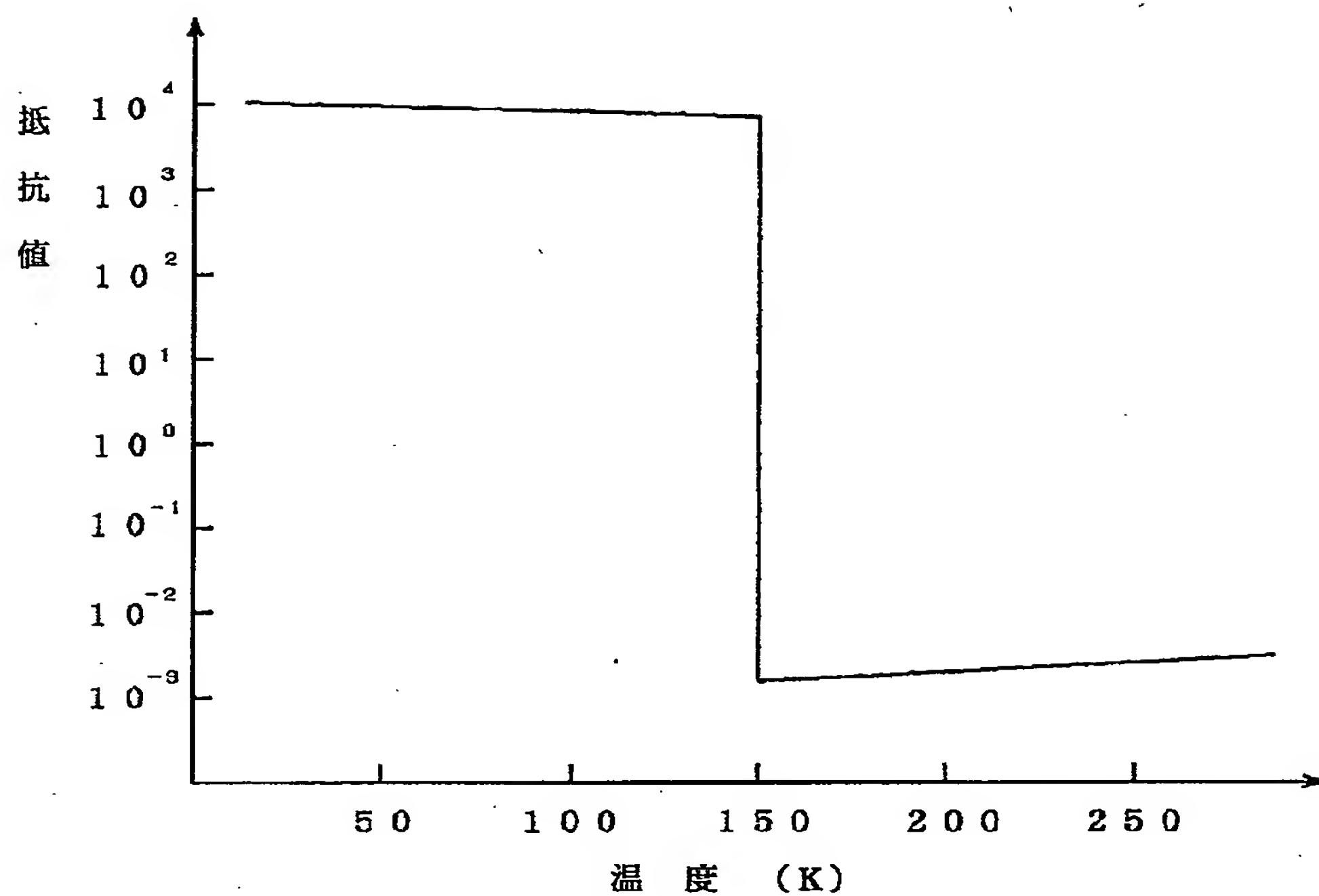
2 銅

3 銅

【図1】



【図2】



## PATENT ABSTRACTS OF JAPAN

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(71)Applicant : NEC CORP

(22)Date of filing : 06.08.1992

(72)Inventor : MIZUKI JUNICHIRO

## (54) TEMPERATURE SENSOR

## (57)Abstract:

PURPOSE: To enable accurate measurement of a temperature simply by sandwiching a substance in which an insulator-metal phase transition occurs at a certain temperature between metals.

CONSTITUTION: Coppers 2 and 3 are evaporated on the top surface and lower surface of an oxide film 1 produced in a film from a substance in which an insulator-metal phase transition occurs at a certain temperature, for example, vanadium oxide to make a sandwich structure, which enables the measuring of a resistance between the coppers 2 and 3. When the vanadium oxide is an insulator, no current flows through the oxide film 1. But when the phase transition occurs at a certain temperature, a large resistance change takes place, which allows the observation of the occurrence of the phase transition simply. The temperature of the phase transition is intrinsic to the oxide film and hence, can be determined as one value accurately. Thus, the temperature can be measured accurately by determining a change in resistance.



## LEGAL STATUS

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decision of rejection]

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**CLAIMS**

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[Claim(s)]

[Claim 1] The thermo sensor characterized by consisting of matter which causes insulator-metal phase transition at a certain temperature, and a metal which puts said matter.

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DETAILED DESCRIPTION

## [Detailed Description of the Invention]

[0001]

[Industrial Application] This invention relates to a thermo sensor.

[0002]

[Description of the Prior Art] When measuring temperature conventionally, the pressure thermometer which used the temperature change of pressures, such as a liquid thermometer using the thermal expansion of a liquid and a gas, as a thermo sensor, the radiation thermometer using thermal radiation, the thermoelectric thermometer using thermoelectromotive force, etc. are reported to a "science study lexicon", the 4th edition, the 1991 publication, and 191 pages.

[0003]

[Problem(s) to be Solved by the Invention] However, since the above-mentioned conventional thermo sensor had a slight change of the sensor output to a temperature change, it had the trouble that it could not be observed with a sufficient precision.

[0004] Furthermore, a certain temperature was observed, when a switch was turned on or turned off, the signal from a thermo sensor had to be changed into an electrical signal, it is more than fixed or below fixed, and there was a trouble of becoming complicated.

[0005] The purpose of this invention solves such a conventional trouble, and is to offer simply the thermo sensor which can measure temperature with a sufficient precision.

[0006]

[Means for Solving the Problem] This invention is characterized by consisting of matter which causes insulator-metal phase transition at a certain temperature, and a metal which puts said matter.

[0007]

[Example] Next, the example of this invention is explained with reference to a drawing.

[0008] Drawing 1 is the cross-sectional view showing one example of the thermo sensor of this invention. The thermo sensor shown in drawing 1 the vanadium oxide (V<sub>2</sub>O<sub>3</sub>) which is the matter which causes insulator-metal phase transition (motto transition) at a certain temperature on the top face and inferior surface of tongue of the vanadium oxide (V<sub>2</sub>O<sub>3</sub>) film 1 which were made into the shape of film Copper (Cu) which is a metal It is made sandwich structure by vapor-depositing 2 and 3, the whole is stuck on a temperature measurement-ed object, and it enables it to measure resistance between copper 2 and 3.

[0009] It is 107 when phase transition happens to a metal at a certain temperature T<sub>c</sub>, although the current did not flow between film when the vanadium oxide (V<sub>2</sub>O<sub>3</sub>) film 1 was an insulator. There is resistance change of extent and it can observe that phase transition happened very simply. The temperature T<sub>c</sub> which causes this phase transition is the thing of a proper, and is correctly set to the vanadium oxide (V<sub>2</sub>O<sub>3</sub>) film 1 at one value. Therefore, temperature can be correctly measured by measuring resistance change.

[0010] Drawing 2 is drawing showing the temperature change of the resistance between the film of this example, and is understood that it is carrying out phase transition to the insulator from the metal at 150 degrees C.

[0011]

[Effect of the Invention] The resistance change accompanying [ as explained above ] phase transition in this invention is 107. Since it becomes extent Although the matter which causes insulator-metal phase transition with temperature was inserted with the metal, while being able to measure temperature very simply and correctly by measuring resistance This resistance change can be changed into current change as it is, and it has the effectiveness that it can use for the switch using a temperature change.

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**DESCRIPTION OF DRAWINGS**

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**[Brief Description of the Drawings]**

[Drawing 1] It is the cross-sectional view showing one example of the thermo sensor of this invention.

[Drawing 2] It is drawing showing the temperature change of the resistance between the film of this example.

**[Description of Notations]**

1 Vanadium Oxide (V<sub>2</sub> O<sub>3</sub>) Film

2 Copper

3 Copper

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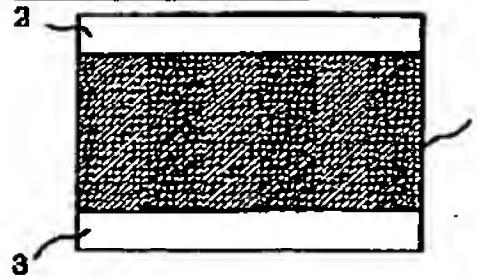
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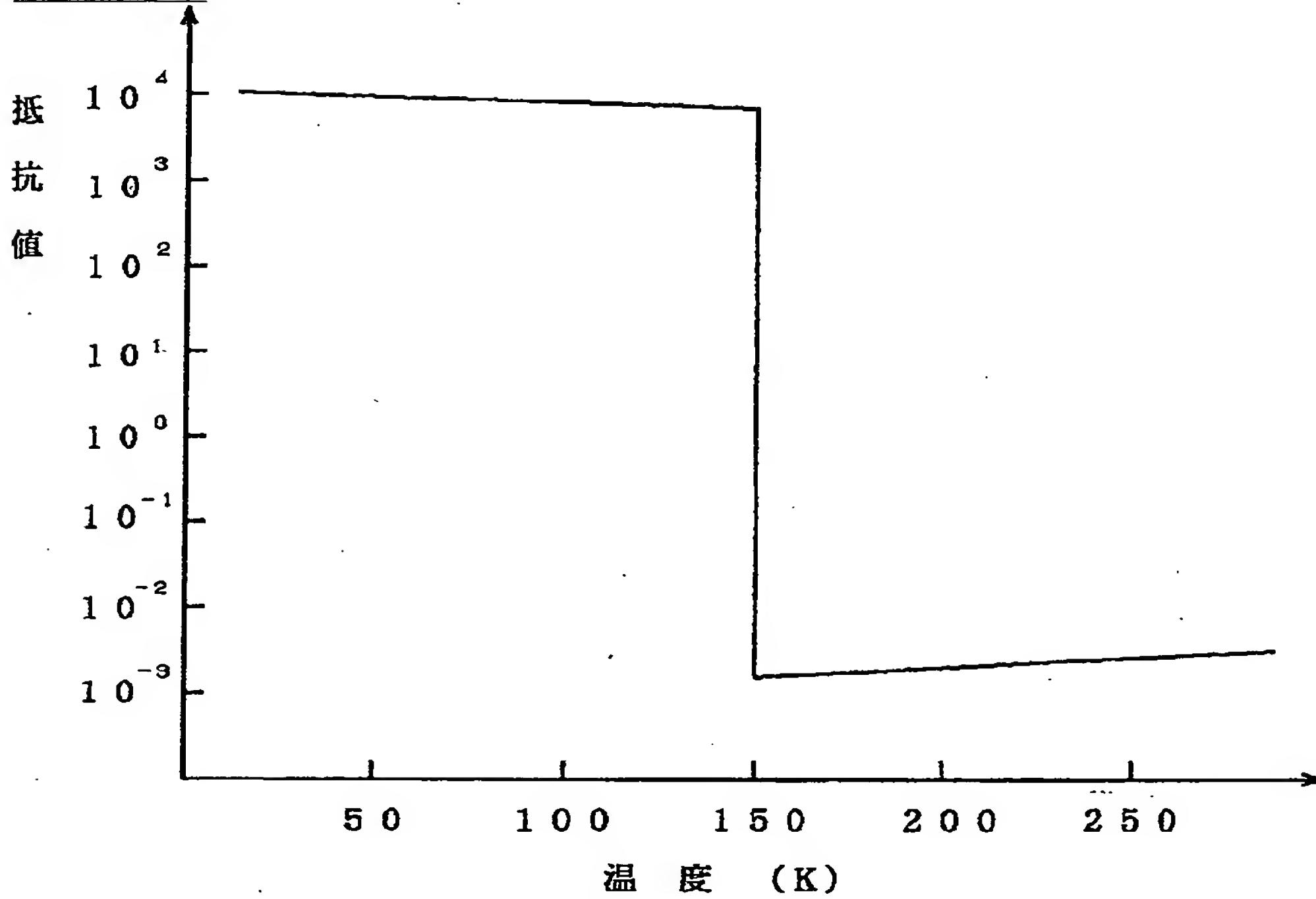
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## DRAWINGS

[Drawing 1]



[Drawing 2]



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